Erratum to: Parity induced edge-current saturation and current distribution in zigzag-edged graphene nano-ribbon devices

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In the original version of this article, Fig. 13 appears incorrectly. The correct version of the figure is given in the right column.

Fig. 13 Electronic band structures in the source and the drain electrodes (*left*) and the transmission probabilities (*right*) of ZGNR *n-i-n* structure with $N = 4$ and $M_{\text{ch}} = 8$ where the source drain bias is $V_{\text{DS}} = 0.5$ [V], and the doping level in the electrode and the channel are $N_{\text{D}}^{\text{S,D}} = 0.03$ and $N_{\text{D}}^{\text{C}} = 0$ per atom, respectively. Results for the ballistic case and the defective case (single edge vacancy near the drain electrode) are compared. Shaded energy range corresponds to the bias window that contributes to the current

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